

APPLICATION DATA SHEET

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Application Type: utility

Title of Invention: METHOD OF FABRICATING SEMICONDUCTOR DEVICE HAVING
GROUP III NITRIDE

Application Number: 09986997

Attorney Docket Number: 740819-617

Legal Representative:

Attorney or Agent: Donald R. Studebaker

Registration Number: 32815

Continuity Data:

This application is a reexamination of 09/389,024 A1 1999-09-02 6,117,700 A1 2000-09-12

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